10/525288 DT13 Rec'd PCT/PT0 16 FEB 2005 PTO

PTO/SB/08A (08-03) se through 07/31/2006, OMB 0651-0031

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Sheet 1

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known						
Application Number	Not yet assigned 10 525,288					
Filing Date Herewith 02/16/2005						
First Named Inventor	James S. Im					
Art Unit	Not yet assigned 2813					
Examiner Name	Not yet assigned Rodgers					
Attorney Docket Number	A35076-PCT-USA (070050 2713)					

Examiner	Cite	Document Number	Publication Date	DOCUMENTS Name of Patentee or	I Bear Oak was Lines 140
Initials*	No.1	Number-Kind Code ^{2 (f known)}	MM-DD-YYYY	Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
(M)	1	^{us-} 5766989	06-16-1998	Maegawa et al.	
60	2	^{US-} 6573531	06-03-2003	Im et al.	
(CO)	3	us- 6322625	11-27-2001	James S. Im	
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		FOREIGI	N PATENT DOCU	MENTS		_
	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	Γ
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Translation is attached.

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Page 1 of 13 Form PTO-14 U.S. Department of Commerce Atty. Docket No. Serial No. atent and Trademark Office A35760-PCT-USA 10/525,288 (070050.2713) INFORMATION DISCLOSURE STATEMENT Applicant BY APPLICANT James S. Im (Use several sheets if necessary) Filing Date Group 02/16/2005 2813 Examiner Rodgers

U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
CO	1.	3632205	01/04/1972	Marcy
CO	2.	4234358	11/18/1980	Celler et al.
.OO	3.	4309225	01/05/1982	Fan et al.
@	4.	4382658	05/10/1983	Shields et al.
(CO)	5.	4456371	06/1984	Lin
0	6.	4639277	01/27/1987	Hawkins
@	7.	4691983	09/08/1987	Kobayashi et al.
@	8.	4727047	02/1988	-Bolzer et al
@	9.	4758533	07/1988	Magee et al.
@	10.	4793694	12/27/1988	Liu
0	11.	4800179	01/1989	Mukai .
©Ø	12.	4855014	08/1989	Kakimoto et al.
œ	13.	4870031	09/1989	Suguhara et al.
(P)	14.	4940505	07/1990	Schachameyer et al.
œ	15.	4970546	11/1990	Suzuki et al.

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· Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office	Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288		
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	Examiner Rodgers			

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
8	16.	4977104	12/11/1990	Sawada et al.
@	17.	5032233	07/1991	Yu et al.
·@	18.	5061655	10/1991	Ipposhi et al.
(OP)	19.	5145808	09/1992	Sameshima et al.
@	20.	5204659	04/1993	Sarma
Ø	21.	5233207	08/1993	Anzai
(CO)	22.	5285236	02/08/1994	Jain
(CP)	23.	5291240	03/1994	Jain
Ø	24.	5304357	04/19/1994	Sato et al.
(Ce)	25.	5373803	12/1994	Noguchi et al.
CO)	26.	5395481	03/1995	McCarthy
(3)	27.	5409867	04/1995	Asano
QQ.	28.	5453594	08/1995	Konecny
æ	29.	5456763	10/1995	Kaschmitter et al.
C	30.	5496768	03/1996	Kudo
Œ	31.	5523193	06/1996	Nelson

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
@	32.	5529951	06/1996	Noguchi et al.
CO	33.	5591668	01/1997	Maegawa et al.
· (20)	34.	5721606	02/01/1998	Jain
(CP)	35.	5742426	04/1998	York
(P)	36.	5756364	05/1998	Tanaka et al.
	37.	-5766989	06/1998	Macgawa et al. duplicated from IDS filed 16 Feb. 2005
CO	38.	5844588	12/1998	Anderson
0	39.	5861991	01/1999	Fork
(P)	40.	5893990	04/1999	Tanaka
(P)	41.	5986807	11/1999	Fork
(CP)	42.	6014944	01/18/2000	-Russelletal: Aklufi et. al.
(P)	43.	6072631	06/2000	Guenther et al.
(Ce)	44.	6081381	06/2000	Shalapenok et al.
(P)	45.	6117752	09/12/2000	Suzuki.
@	46.	6120976	09/2000	Treadwell et al.
CR	47.	6130009	10/2000	Smith et al.

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Examiner	Collect& Col	Date Considered	23 March 2007	

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	Examiner		

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
æ	48.	6130455	10/10/2000	Yoshinouchi
@	49.	6156997	12/2000	Yamazaki et al.
@	50:	6162711	12/19/2000	Ma et al.
.00	51.	6169014	01/2001	McCulloch
(CP)	52.	6172820	01/2001	Kuwahara.
(A)	53.	6177301	01/2001	Jung
@	54.	6187088	02/01/2001	Okumura
œ	55.	6190985	02/2001	Buynoski
(CP)	56.	6193796	02/01/2001	Yang
æ	57.	6203952	03/2001	O'Brien et al.
œ	58.	6235614	02/01/2001	Yang
(CO)	59.	6242291	06/2001	Kusumoto et al.
œ	60.	6285001	09/2001	Fleming et al.
æ	61.	6300175	10/2001	Moon
OP.	62.	6313435	11/2001	Shoemaker et al.
©	63.	6316338	11/2001	Jung

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Examiner College Col	Date Considered	23 March 2007

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
(CR)	64.	6320227	11/2001	Lee et al.
	-65.	6322625	11/2001	Im duplicated from IDS filed 16 Feb. 2005
·@	66.	6326186	12/2001	Parketal. Kirk et al.
<u>@</u>	67.	6326286	12/2001	Park et al.
@	68.	6333232	12/2001	Kunikiyo
@	69.	6368945	04/09/2002	Im .
(Ce)	70.	6388146	05/14/2002	Onishi et al.
@	71.	6407012	06/18/2002	Miyasaka et al.
@	72.	6444506	09/2002	Kusumoto et al.
(P)	73.	6468845	10/22/2002	Nakajima et al.
(CR)	74.	6495067	12/17/2002	Ono
(P)	75.	6511718	01/18/2003	Paz de Araujo et al.
00	76.	6521492	02/18/2003	Miyasaka et al.
(e)	77.	6528359	03/2003	Kusumoto et al.
œ	78.	6555449	04/2003	Im et al.
	_79	6573531	06/2003	Inverse. Duplicated from IDS filed

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
œ	80.	6621044	09/01/2003	Jain et al.
@	81.	6635554	10/2003	Im et al.
·@	82.	6526585	03/04/2003	Hill
@	83.	20010001745	05/24/2001	Im et al.
@	84.	20010041426	11/15/2001	lm
(CR)	85.	20040053450	03/18/2004	Sposili et al.
@	86.	20020104750	08/08/2002	Ito
(CP)	87.	RE33836	03/03/1992	Resor, III et al.
	88.	-60/253256	08/31/2003	Im
@	89.	2003096489	05/22/2003	Im et al.
(ce)	90.	2003119286	06/26/2003	Im et al.
(A)	91.	2005032249	02/10/2005	lm et al.
@	92.	2003029212	02/13/2003	Im
œ	93.	2004061843	04/01/2004	lm
œ	94.	2005034653	02/17/2005	Im et al.
@	95.	6563077	05/13/2003	Im

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Examiner Collectical	Date Considered 23 March 2007

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
@	96.	6582827	06/24/2003	lm .
8	97.	6830993	12/14/2004	Im et al.
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FOREIGN PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Country	<u>Translation</u> Yes No
@	98.	681316	08/11/1995	EP	
00	99.	1067593	10/01/2001	EP	
OP	100.	655774	07/17/1996	EP	
0	101.	2338343	12/15/1999	GB	
@	102.	2338597	12/22/1999	GB	,
(A)	103.	2338342	12/15/1999	GB	
@	104.	2283036	11/20/1990	JP	No
@	105.	6252048	09/09/1994	JP	No
©	106.	6283422	10/07/1994	JP	No
(OP)	107.	7176757	07/14/1995	JP	· <u>No</u>
œ	108.	11064883	03/05/1999	JP	<u>No</u>
@	109.	04033327		JP	No ·
œ	110.	2001023920	01/26/2001	JP	
Œ	111.	62181419	08/08/1987	JP	
(W)	112.	9824118	- 06/04/1998	wo	

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	Examiner Rodgers		

Exam Initial	No.	Document No.	Publication Date	Country	<u>Translation</u> Yes No
®	113.	9931719	06/24/1999	wo	<u>No</u>
@	114.	0014784	03/16/2000	wo	
·O	115.	0118854	03/15/2001	wo	
œ	116.	0118855	03/15/2001	wo	
(R)	117.	0171786	09/27/2001	wo	
@	118.	02031869	04/18/2002	wo	
@	119.	02086954	05/30/2002 10/31/2002	wo	
@	120.	9745827	12/04/1997	wo	,
@	121.	0242847	05/30/2002	wo	·
@	122.	03046965	06/05/2003	wo	
@	123.	02086955	10/31/2002	wo	
@	124.	03018882	03/06/2003	wo	
@	125.	04017379	02/26/2004	wo	
œ	126.	03084688	10/16/2003	wo	
00	127.	04017382	02/26/2004	wo	
(A)	128.	04017381	02/26/2004	wo	

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Exam Initial	No.	Document No.	Publication Date	Country	<u>Translation</u> Yes No
@	129.	04017380	02/26/2004	wo	
(A)	130.	04075263	08/19/2003	WO	

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Date Considered 23 March 2007

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	Examiner RodgerS		
	3		

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
(ca)	131.	Im et al., "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", Phys. Stat. Sol. (a), vol. 166, p. 603 (1998).
@	132.	S.D. Brotherton et al., "Influence of Melt Depth in Laser Crystallized Poly-Si Thin Film Transistors," 82 J. Appl. Phys. 4086 (1997).
(CP)	133.	J.S. Im et al., "Crystalline Si Films for Integrated Active-Matrix Liquid-Crystals Displays," 21 MRS Bulletin 39 (1996).
@	134.	Im et al., "Single-Crystal Si Films for Thin-Film Transistor Devices," Appl. Phys. Lett., Vol 70 (25), p. 3434 (1997).
(CP)	135.	Sposili et al., "Sequential Lateral Solidification of Thin Silicon Films on SiO2", Appl, Phys. Lett., vol. 69 (19), p. 2864 (1996).*
(P)	136.	Crowder et al., "Low-Temperature Single-Crystal Si TFT's Fabricated on Si Films processed via Sequential Lateral Solidification", IEEE Electron Device Letter, vol. 19 (8), p. 306 (1998).*
©	137.	Sposili et al., "Single-Crystal Si Films via a Low-Substrate-Temperature Excimer-Laser Crystallization Method", Mat. Res. Soc. Symp. Proc. vol. 452, pp. 953-958, 1997 Materials Reasearch Society.*
œ	138.	C. E. Nebel, "Laser Interference Structuring of A-SI:h" Amorphous Silicon Technology1996, San Francisco, CA Apr. 8-12, 1996, Materials Research Society Symposium Proceedings, vol. 420, Pittsburgh, PA.
@	139.	J. H. Jeon et al., "Two-step laser recrystallization of poly-Si for effective control of grain boundaries", Journal of Non Crystalline Solids, North-Holland Publishing Company, NL, vol. 266-269, May 2000, pp. 645-649.
@	140.	H. Endert et al., "Excimer Laser: A New Tool for Precision Micromaching," 27 Optical and Quantum Electronics, 1319 (1995).

NY02:5439				
Examiner	Collentable	Date Considered	23 March 2007	

^{*} Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Examiner Rodges		

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
(ce	141.	"Overview of Beam Delivery Systems for Excimer Lasers," Micro/Las Lasersystem GMBH. 1999	
CO.	142.	K.H. Weiner et al., "Ultrashallow Junction Formation Using Projection Gas Immersion Laser Doping (PGILD)," A Verdant Technologies Technical Brief, Aug. 20, 1997.	
œ	143.	Hau-Riege C.S. et al., "The Effects Microstructural Transitions at Width Transitions on interconnect reliabity," Journal of Applied Physics, June 15, 2000, vol. 87, no. 12, pp. 8467-8472	
Ge Ge	144.	McWilliams et al., "Wafer-Scale Laser Pantography: Fabrication of N-Metal-Oxide-Semiconductor Transistors and Small-Scale Integrated Circuits By Direct-Write Laser-Induced Pyrolytic Reactions," Applied Physics Letters, American Institute of Physics, New York, US, vol. 43, no. 10, Nov. 1983, pp. 946-948	
Ca	145.	Mariucci et al., "Grain boundary location control by patterned metal film in excimer laser crystallized polysilicon," Proceedings of the Figth International Conference on Polycrystalline Semiconductors, Schwabisch Gmund, Germany, Sept. 13-18, 1998, vol. 67-68, pp. 175-180	
@	146.	Broadbent et al., "Excimer Laser Processing of Al-1%Cu/TiW Interconnect Layers," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, Santa Clara, CA, June 12-13, 1989, pp. 336-345	
@	147.	H.J. Kim and James S. Im, "Grain Boundary Location-Controlled Poly-Si Films for TFT Devices Obtained Via Novel Excimer Laser Process," Abstracts for Symposium of Materials Research Society, Nov.27 to Dec. 2, 1994, p. 230.	
	148.	S.D. Brotherton, "Polycrystalline Silicon Thin Film Transistors," 10 Semicond. Sci. Tech., pp. 721-738 (1995).	
Œ	149.	H. Watanabe et al., "Crystallization Process of Polycrystalline Silicon by KrF Excimer Laser Annealing," 33 Japanese J. of Applied Physics Part 1Regular Papers Short Notes & Review Papers, pp. 4491-98 (1994).	
	150.	E. Fogarassy et al., "Pulsed Laser Crystallization of Hydrogen-Free a-Si Thin Films for High-Mobility Poly-Si TFT Fabrication," 56 Applied Physics ASolids and Surfaces, pp. 365-373 (1993).	

NY02:543906.1	· · · · · · · · · · · · · · · · · · ·	
Examiner College Col	Date Considered 23 Warch 2007	

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)		
@	151.	Y. Miyata et al, "Low-Temperature Polycrystalline Silicon Thin-Film Transistors for Large-Area Liquid Crystal Display," 31 Japanese J. of Applied Physics Part 1Regular Papers Short Notes & Review Papers, pp. 4559-62 (1992).		
.OP	152.	Im et al., "Phase Transformation Mechanisms Involved in Excimer Laser Crystallization of Amorphous Silicon Films," Appl. Phys. Lett., Vol. 63 (14), p. 1969 (1993).		
(Ce)	153.	Im et al., "On the Super Lateral Growth Phenomenon Observed in Excimer Laser-Induced Crystallization of Thin Si Films," Appl. Phys. Lett., Vol. 64 (17), p. 2303 (1994).		
@	154.	Brochure from MicroLas Lasersystem, GmbH, "UV Optics Systems for Excimer Laser Based Micromaching and Marking". 1999.		
@	155.	Ishida et al., "Ultra-shallow boxlike profiles fabricated by pulsed ultraviolet-laser doping process", J. Vac. Sci. Technol. B 12(1), p. 399-403, 1994. (No month).		
@	156.	Yoshimoto, et al., "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, AM-LCD 2000. No month.		
@	157.	Ozawa et al., "Two-Dimensionally Position-Controlled Exicer-Laser-Crystallization of Silicon Thin Films on Glassy Substrate", Jpn. J. Appl. Phys. vol. 38, Part 1, No. 10, p. 5700-5705, (1999). No month.		
@	158.	I.W. Boyd, Laser Processing of Thin Films and Microstructures, Oxidation, Deposition, and Etching of Insulators (SpringerVerlag Berlin Heidelber 1987).*		
œ	159.	N. Yamamuchi and R. Reif, Journal of Applied Physics, "Polycrystalline silicon thin films processed with silicon ion implantation and subsequent solid-phase crystallization: Theory, experiments, and thin-film transistor applications" April 1, 1994 Volume 75, Issue 7, pp. 3235-3257		
œ	160.	T. Noguchi, "Appearance of Single-Crystalline Properties in Fine-Patterned Si Thin Film Transistors (TFTs) by Solid Phase Crystallization (SPC)," Jpn. J. Appl. Phys. Vol. 32 (1993) L1584-L1587		
(Co)	161.	Ishihara et al., "A Novel Double-Pulse Exicem-Laser Crystallization Method of Silicon Thin-Films," Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 34, no. 8A, August 1995, pp. 3976-3981		
OP	162.	Kim, H. J., "Excimer-Laser-Induced Crystallization of Amorophus Silicon Thin Films", Ph. D. Dissertation Abstract, Columbia University, 1996.*		

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Examiner College Colle	Date Considered	28-March 2007

^{*} Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.